

# Ryosuke Kikuchi

## List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Investigation of the Acceleration and Suppression of the Light-Induced Degradation of a Lead Halide Perovskite Solar Cell Using Hard X-ray Photoelectron Spectroscopy. ACS Applied Energy Materials, 2022, 5, 4125-4137.	5.1	4
2	SrZn <sub>2</sub> N <sub>2</sub> as a Solar Absorber: Theoretical Defect Chemistry and Synthesis by Metal Alloy Nitridation. Chemistry of Materials, 2021, 33, 2864-2870.	6.7	12
3	Theoretical Prediction and Thin-Film Growth of the Defect-Tolerant Nitride Semiconductor YZn <sub>3</sub> N <sub>3</sub> . Chemistry of Materials, 2021, 33, 8205-8211.	6.7	7
4	Evaluation of Band Alignment of SrNbO <sub>2</sub> N Using Hard X-ray Photoelectron Spectroscopy. Journal of Physical Chemistry C, 2020, 124, 5528-5532.	3.1	5
5	Two-step epitaxial growth of NbON (100) thin films on rutile-type TiO <sub>2</sub> (101) substrates and reduction of residual carrier concentration by RF reactive sputtering. CrystEngComm, 2019, 21, 3552-3556.	2.6	3
6	Fundamental Semiconducting Properties of Perovskite Oxynitride SrNbO <sub>2</sub> N: Epitaxial Growth and Characterization. Chemistry of Materials, 2017, 29, 7697-7703.	6.7	17
7	Characterization of Baddeleyite-structure NbON Films Deposited by RF Reactive Sputtering for Solar Hydrogen Production Devices. Electrochemistry, 2015, 83, 711-714.	1.4	12
8	Coherent Growth of AlN/GaN Short-Period Superlattice with Average GaN Mole Fraction of up to 20% on 6H-SiC(0001) Substrates by Plasma-Assisted Molecular-Beam Epitaxy. Japanese Journal of Applied Physics, 2013, 52, 08JE21.	1.5	4
9	AlN/GaN Short-Period Superlattice Coherently Grown on 6H-SiC(0001) Substrates by Molecular Beam Epitaxy. Applied Physics Express, 2012, 5, 051002.	2.4	3